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| APPLICATION NO. | FILING DATE | FIRST NAMED INVENTOR | ATTORNEY DOCKET NO. | CONFIRMATION NO. |
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| 09/429,283 | 10/28/1999 | SHUICHI UENO | 0057-2534-2Y | 5740 |

22850 7590 05/30/2003

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| FOURSON III, GEORGE R |

| ART UNIT | PAPER NUMBER |
|---|---|
| 2823 | |

DATE MAILED: 05/30/2003

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| EXAMINER | |
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| ART UNIT | PAPER |
| | 26 |

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**Commissioner for Patents**

The appendix to the Appeal Brief filed 5/20/02 contains the following errors in the listing of the claims on appeal. In claim 14, lines 12, 13 and 15, --active-- should appear before "region".

Please see attached copy of the translation of Japan '766.

The correct listing of the Prior Art of Record in the Examiner's Answer mailed 10/02/02 is as follows:

Kuroi, T., et al., "The Impact of Nitrogen Implantation into Highly Doped Polysilicon Gates for Highly Reliable and High-Performance Sub-Quarter-Micron Dual Gate Complementary Metal Oxide Semiconductor",Japanese Journal of Appl. Phys., Vol.34 (February 1995), pp.771-775

Sze, S.M., "VLSI Technology", second edition, McGraw Hill (1988), pp. 493-494

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Art Unit: 2823